

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	196893	(station\$1 module\$1 chamber\$1) same ((wet\$3 wetting) electro\$1less overburden\$3 activat\$3 reclaim\$3 repair\$3 initiat\$3 seed\$3 nucleat\$3) same ((wet\$3 wetting) electro\$1less overburden\$3 activat\$3 reclaim\$3 repair\$3 initiat\$3 seed\$3 nucleat\$3)	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2004/12/09 14:02
L2	8579	1 and (power voltage\$1 potential\$1 current\$1) near7 (suppl\$3 equipment\$1 device\$1 apparat\$3) near10 (distinct different second another)	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2004/12/09 13:25
L3	2595	2 and semiconduct\$3	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2004/12/09 13:36
L4	857	3 and ((power voltage\$1 potential\$1 current\$1) near3 (suppl\$3 equipment\$1 device\$1 apparat\$3) near5 (distinct different second another)) and (electro\$1plat\$3 plat\$3)	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2004/12/09 13:37
L5	425	4 and semiconduct\$3 near3 (process\$2 method\$1 manufactur\$3)	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2004/12/09 13:37
L6	425	5 and ((power voltage\$1 potential\$1 current\$1) near3 (suppl\$3 equipment\$1 device\$1 apparat\$3) near5 (distinct different second another))	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2004/12/09 13:47
L7	425	6 and ((power voltage\$1 potential\$1 current\$1) near3 (suppl\$3 equipment\$1 device\$1 apparat\$3) near5 (distinct different second another))	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2004/12/09 13:48
L8	233	1 and overburden\$3 same (second\$1 minute\$1)	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2004/12/09 14:03
L9	233	8 and overburden\$3 same (second\$1 minute\$1)	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2004/12/09 14:03
L10	8	("257"/\$.ccls. "438"/\$.ccls. "427"/\$.ccls.) and 9	USPAT	OR	OFF	2004/12/09 14:05

S1	196563	(station\$1 module\$1 chamber\$1) same ((wet\$3 wetting) electro\$1less overburden\$3 activat\$3 reclaim\$3 repair\$3 initiat\$3 seed\$3 nucleat\$3) same ((wet\$3 wetting) electro\$1less overburden\$3 activat\$3 reclaim\$3 repair\$3 initiat\$3 seed\$3 nucleat\$3)	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2004/12/09 13:20
S2	79031	S1 and (station\$1 module\$1 chamber\$1) same first same second	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2004/12/07 14:14
S3	11747	S2 and semiconductor	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2004/12/07 14:14
S4	112	S3 and (electrolyte\$1 near7 (composition concentration make near2 "up"))	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2004/12/07 14:20
S5	112	S4 and (electrolyte\$1 near7 (composition concentration make near2 "up"))	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2004/12/07 14:20